

# United States Patent and Trademark Office

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.		FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/078,473	-	02/21/2002	Hoki Kwon	15436.438.1	4854	
22913	7590	08/03/2006		EXAMINER		
WORKMA			NGUYEN, DUNG T			
(F/K/A WO 60 EAST S		NYDEGGER & S EMPLE	ART UNIT	PAPER NUMBER		
1000 EAGI			2828			
SALT LAK	E CITY,	UT 84111	DATE MAILED: 08/03/2006			

Please find below and/or attached an Office communication concerning this application or proceeding.

•				Ox-
	Application	on No.	Applicant(s)	
	10/078,47	73	KWON, HOKI	
Office Action Summary	Examiner		Art Unit	
		chael) T. Nguyen	2828	
The MAILING DATE of this commu Period for Reply	nication appears on the	ecover sheet with the	correspondence add	ress
A SHORTENED STATUTORY PERIOD I WHICHEVER IS LONGER, FROM THE I Extensions of time may be available under the provision after SIX (6) MONTHS from the mailing date of this common of the period for reply is specified above, the maximum service of the period for reply within the set or extended period for reply any reply received by the Office later than three months earned patent term adjustment. See 37 CFR 1.704(b).	MAILING DATE OF TH is of 37 CFR 1.136(a). In no evolution imunication. statutory period will apply and will by will, by statute, cause the app	HIS COMMUNICATIO ent, however, may a reply be ti ill expire SIX (6) MONTHS from lication to become ABANDONE	N. mely filed n the mailing date of this cor ED (35 U.S.C. § 133).	
Status				
<ol> <li>Responsive to communication(s) file</li> <li>This action is FINAL.</li> <li>Since this application is in condition closed in accordance with the practice.</li> </ol>	2b)⊠ This action is n n for allowance except	for formal matters, pr		merits is
Disposition of Claims				
4) ☐ Claim(s) 1-21 is/are pending in the 4a) Of the above claim(s) is/s 5) ☐ Claim(s) 1-7 and 13-21 is/are allow 6) ☐ Claim(s) 8-10,12 is/are rejected. 7) ☐ Claim(s) 11 is/are objected to. 8) ☐ Claim(s) are subject to restrict the specification is objected to by the specification is objected to be supplied to the specification is objected to be specification.	are withdrawn from coned.			
10) The drawing(s) filed on is/are Applicant may not request that any objected from the control of the co	e: a) accepted or b) ection to the drawing(s) b g the correction is require	ne held in abeyance. Se ed if the drawing(s) is ob	e 37 CFR 1.85(a). njected to. See 37 CFF	` '
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a claim a) All b) Some * c) None of:  1. Certified copies of the priority 2. Certified copies of the priority 3. Copies of the certified copies application from the Internation* * See the attached detailed Office actions.	y documents have bee y documents have bee s of the priority docume onal Bureau (PCT Rule	n received. n received in Applicat ents have been receive e 17.2(a)).	ion No ed in this National S	stage
Attachment(s)  1) ☑ Notice of References Citèd (PTO-892)		4) Interview Summary	(PTO-413)	
2) Notice of Draftsperson's Patent Drawing Review ( 3) Information Disclosure Statement(s) (PTO-1449 o Paper No(s)/Mail Date	•	Paper No(s)/Mail D  5) Notice of Informal F  6) Other:	ate	152)

### **DETAILED ACTION**

### Response to Arguments

Applicant's arguments with respect to claims 8-12 have been considered but are moot in view of the new ground(s) of rejection.

## Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claim 8 is rejected under 35 U.S.C. 102(b) as being anticipated by Inata et al. (5266814). Inata et al. disclose in Fig.3 and 11 a tunnel junction A2-A4 having a p-doped (it is understood that Inata et al. disclose a resonant-tunneling transistor with the n-doped emitter A1 and the n-doped collector A5 (i.e., a bipolar n-p-n transistor). Therefore, the base A2-A4 must be p-doped) GaAs(1-x)Sbx layer A2 less than 10 nm thick (col.5, 1.24-37 and col.6, 1.5-8).

#### Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person

having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 9-10 and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Inata et al. (5266814) in view of McDermott et al. (Growth and doping of GaAsSb via metalorganic chemical vapor deposition for InP heterojunction bipolar transistors in Appl. Phys. Lett., Vo1.68, No. 10, 4 March 1996).

With respect to claim 9, Inata et al. disclose all limitations of the claims except for doping with carbon with a concentration greater than 1x10sub19 cm-3.

McDermott et al. teach doping with carbon with a concentration greater than 1x10sub19 cm-3 (first column, page 1386).

it would have been obvious to one having ordinary skill in the art at the time the invention was made to provide Inata et al. what is taught by McDermott et al. to meet the requirement for n-p-n bipolar transistor (first column, page 1386).

With respect to claims 10 and 12, Inata et al. disclose an InP A4' in Fig. 12.

### Allowable Subject Matter

Claim 11 is objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

Claims 1-7 and 13-21 are allowed.

The following is an examiner's statement of reasons for allowance:

Application/Control Number: 10/078,473 Page 4

Art Unit: 2828

Claim 1 is allowed over the Inata et al. and McDermott et al. prior art because they fail to teach a method of fabricating a tunnel junction of a VCSEL comprising locating a substrate in an

MOCVD chamber and setting a temperature between 500 and 650 degrees C, and growing a

tunnel junction GaAs(1-x)Sbx.

Claim 13 is allowed over the Inata et al. and McDermott et al. prior art because they fail

to teach a VCSEL comprising an active region having a plurality of quantum wells and a tunnel

junction over said active region, wherein said tunnel junction includes GaAs(1-x)Sbx layer.

Claims 2-7 and 14-21 are found allowable due to their dependency of claims 1 and 13.

Communication Information

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Dung (Michael) T Nguyen whose telephone number is (571) 272-1949. The examiner can normally be reached on 8:30 - 17:00.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Min Harvey can be reached on (571) 272-1835. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 306-3329.

Midael M

Michael Dung Nguyen

07/26/06